ST KSB564

PNP Silicon Epitaxial Planar Transistor

Audio Frequency Power amplifier applications.

The transistor is subdivided into three group, O, Y and G according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package Weight approx. 0.19g

Absolute Maximum Ratings (Ta=25℃)

	Symbol	Value	Unit
Collector Base Voltage	-V _{CBO}	30	V
Collector Emitter Voltage	-V _{CEO}	25	V
Emitter Base Voltage	-V _{EBO}	5	V
Collector Current	-I _C	800	mA
Power Dissipation	P _{tot}	625	mW
Junction Temperature	Tj	150	°C
Storage Temperature Range	Ts	-55 to +150	°C







Dated : 07/12/2002

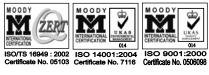
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Characteristics at $T_{amb}=25$ °C

	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain					
at -V _{CE} =1V, -I _C =100mA					
Current Gain Group O	h_{FE}	70	-	140	-
Y	h _{FE}	120	-	240	-
G	h _{FE}	200	-	400	-
Collector Emitter Breakdown Voltage					
at -I _c =10mA	-V _{(BR)CEO}	25	-	-	V
Collector Base Breakdown Voltage					
at -I _C =100μA	-V _{(BR)CBO}	30	-	-	V
Emitter Base Breakdown Voltage					
at -I _E =100µA	-V _{(BR)EBO}	5	-	-	V
Collector Cutoff Current					
at -V _{CB} =30V	-I _{CBO}	-	-	0.1	μA
Collector Saturation Voltage					
at -I _C =500mA, -I _B =50mA	-V _{CE(sat)}	-	-	0.5	V
Base Saturation Voltage					
at -I _C =500mA, -I _B =50mA	-V _{BE(sat)}	-	-	1.2	V
Collector Output Capacitance					
at -V _{CB} =6V, f=1MHz	C _{OB}	-	18	-	pF
Transition Frequency					
at -V _{CE} =6V, -I _C =10mA	f _T	-	110	-	MHz







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